

Attorney's Docket No.: 07043-060002

Client's Ref. No.: B97-065-2

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Number of pages including this page 3

Applicant : Brosnihan et al

Serial No. : 09/342,348

Filed : June 29, 1999

Art Unit : 2814

Examiner : Anh D. Mai

Title : METHOD OF FABRICATING A MICROFABRICATED HIGH ASPECT
RATIO DEVICE WITH ELECTRICAL ISOLATION

MAIL STOP AMENDMENT

Commissioner for Patents

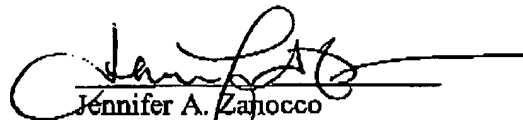
P.O. Box 1450

Alexandria, VA 22313-1450

Attached to this facsimile communication cover sheet is Reply to Examiner Interview
Summary mailed June 2, 2005, faxed this 17th day of June, 2005, to the United States Patent and
Trademark Office.

Respectfully submitted,

Date: June 17, 2005


Jennifer A. Zahocco
Reg. No. 54,563

Customer No. 26181

Fish & Richardson P.C.

Telephone: (650) 839-5070

Fax: (650) 839-5071

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Title : METHOD OF FABRICATING A MICROFABRICATED HIGH ASPECT RATIO
DEVICE WITH ELECTRICAL ISOLATION**Mail Stop Amendment**

Commissioner for Patents

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REPLY TO INTERVIEW SUMMARY OF JUNE 2, 2005

In reply to the Interview Summary of June 2, 2005, the Applicants submit the following remarks.

The Applicants discussed amending claim 1 to include a step of etching a first trench in single crystal silicon, a step of depositing a dielectric isolation layer in the first trench and a step of etching a second trench in the single crystal silicon, the etching of the second trench to be performed after depositing the dielectric isolation layer. Bashir etches two trenches 120, 121 simultaneously in a silicon layer 106. Bashir does not perform two separate etching steps in the silicon layer 106.

In the Interview Summary, the Examiner states that the "Applicants will amend the claim to distinguish from the reference namely the two trenches will be formed at the different process steps."

Applicants do not admit that this amendment was required to distinguish the claims from U.S. Patent No. 5,747,353 ("Bashir"). The Applicants have provided, in previous written communications with the Examiner, reasons that Bashir does not disclose at least one of the limitations required by claim 1. The amendment was made to further prosecution.

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Page : 2 of 2


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Jennifer A. Zanicco
Reg. No. 54,563

Customer No. 26181
Fish & Richardson P.C.
Telephone: (650) 839-5070
Facsimile: (650) 839-5071

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